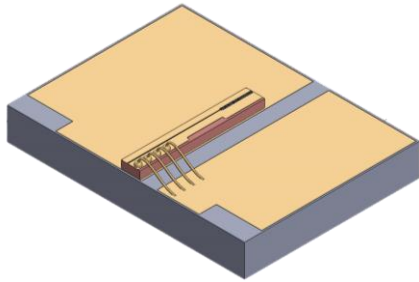
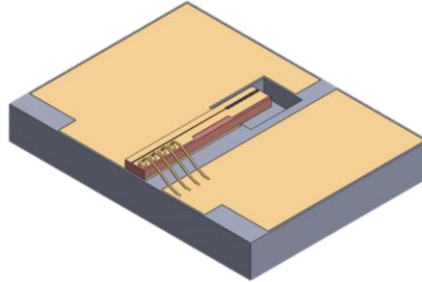


Specification Sheet | 778.105 nm Series

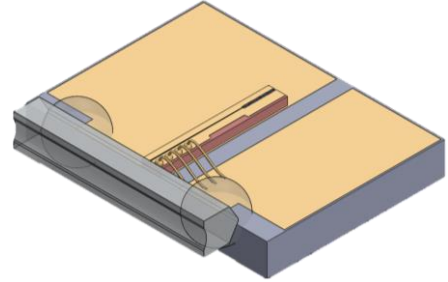
Distributed Bragg Reflector (DBR) Laser Diode



Chip on Submount (CoS)



CoS + Mode-Hop Free (MHF)



CoS + Virtual Point Source (VPS) Lens

Description

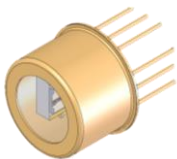
The 778.105 nm DBR Series of high-performance edge-emitting laser diodes are based on Photodigm’s advanced monolithic single-frequency Gallium Arsenide (GaAs) based laser technology. It provides a single spatial mode beam and has passivated facets for reliability. The 778.105 nm Series DBR devices are used in atomic spectroscopy for rubidium-based (Rb) applications. The 778.105 nm Series DBR devices are Spectroscopy Certified; guaranteed to hit the Rb two-photon transition (2PT) ± 10 °C from room temperature.

778.105 nm DBR Chip on Submount (CoS) Characteristics

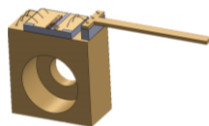
Parameters ¹	Chip Architecture
	High Power
Wavelength, Nominal (nm) ²	778.105 \pm 0.6
Power Range (mW)	80–180
Operating Current, Max (CW & Pulsed) (mA)	250
Optical Power at Max Operating Current (mW)	180
Slope Efficiency, Nominal (W/A)	0.85
Threshold Current, Nominal (mA)	50

1. Characteristics at T_c = 25 °C unless otherwise specified. Operating outside of these parameters voids warranty.
 2. Hermetically sealed packages may contain CoS that are ± 1.2 nm from nominal.

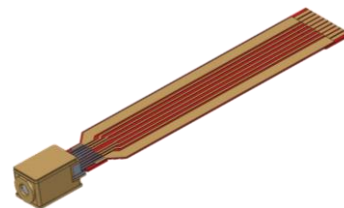
Available Free-Space Package Add-ons



TO-8



C-Mount



Transmitter Optical Subassembly (TOSA)

Specification Sheet | 778.105 nm Series

Distributed Bragg Reflector (DBR) Laser Diode

Specifications

Laser

Parameter	Unit	Min	Typical	Max
Storage Temperature	°C	0	-	70
Operating Temperature at case	°C	5	-	70
Operating Temperature at laser chip ¹	°C	5	-	45
Laser Series Resistance	Ω	-	2	-
Laser Forward Voltage @ LIV Current	V	-	2	-
Nominal Laser Linewidth @ LIV Current	kHz	-	500	-
Beam Divergence @ FWHM ($\theta_{ } \times \theta_{\perp}$)	°	-	6 x 28	8 x 32
Side Mode Suppression Ratio (SMSR)	dB	-	-40	-
Polarization Extinction Ratio	dB	-17	-20	-
Laser Polarization	TE			
Mode Structure	Fundamental Mode			
Temperature Tuning Rate	nm/°C	-	0.06	-
Current Tuning Rate	nm/mA	-	0.002	-
Laser Reverse Voltage	V	-	-	0

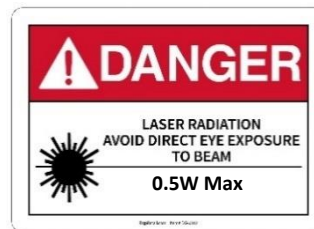
1. Operation below dew point not recommended without hermetically sealed packaged

Free-Space Package Add-Ons

Parameter	Unit	Min	Typical	Max
Photodiode Forward Current	mA	-	-	10
Photodiode Reverse Voltage	V	-	-	50
TEC Current (TOSA)	A	-1.1	-	1.1
TEC Voltage (TOSA)	V	-3.0	-	3.0
TEC Current (TO-8)	A	-1.8	-	1.8
TEC Voltage (TO-8)	V	-2.2	-	2.2
Thermistor Resistance	kΩ	-	10	-

Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic container with all leads shorted together.

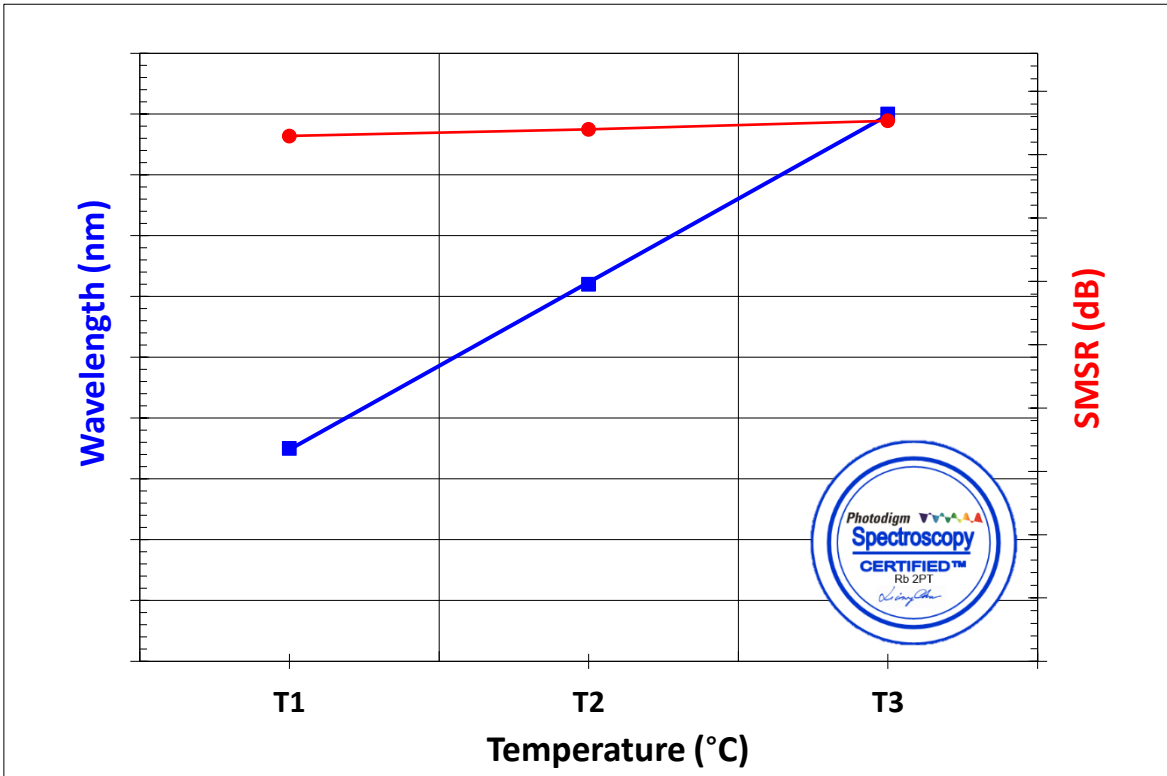


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Specification Sheet | 778.105 nm Series

Distributed Bragg Reflector (DBR) Laser Diode

Air Wavelength Characteristics at Constant Current by Temperature



LIV Characteristics by Current

